



A Product Line of **Diodes Incorporated** 

# LITE-ON SEMICONDUCTOR G15H150D5

TRENCH SCHOTTKY RECTIFIER				REVERSE V		– 150 Voli – 15 Amp	
FEATURES					PowerDI5		
Super Low Forward Vol			<u> </u>				
Reliable High Temperat							
Softest, fast switching of					K		
<ul> <li>150°C Operation Juncti</li> </ul>		e				~	
Qualified according to A					2		
<ul> <li>Lead-Free Finish; Rol</li> </ul>							
<ul> <li>Halogen and Antimon</li> </ul>	y Free. "Greer	n" Device (Note	3)				
						2 1	
						-	
APPLICATION						_	
Device optimized for ult				Top Viev	V	Bottom View	
to maximize efficiency in	r Power Supply	application					
MECHANICAL DATA							
Package: PowerDI5							
Package Material: "Gre	en" molding co	mpound III flam	nmability	PINK		PIN1 (A)	
classification 94V-0,"Ha					Ì <b>⊲</b> -		
Moisture Sensitivity Lev		-020		Case		PIN2 (A)	
Lead free finish, RoHS							
Weight: 0.1 grams (App							
<ul> <li>Marking code: G15H15</li> </ul>	0						
MAXIMUM RATINGS ANI							
MAXIMUM RATINGS ANI Ratings at 25°C ambient te							
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS			e specified.		VALUE		
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS PARA	D ELECTRICA emperature ur METER				<b>VALUE</b> 150		UNIT
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS PARA Maximum repetitive peak reverse	D ELECTRICA emperature ur METER		e specified.				
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS PARA	D ELECTRICA emperature ur METER e voltage		e specified.		150		V
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS PARA Maximum repetitive peak reverse Maximum DC blocking voltage	D ELECTRICA emperature ur METER e voltage ut current	nless otherwise	SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub>		150 150 15		V V A
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpu Peak forward surge current 8.3m superimposed on rated load.	D ELECTRICA emperature ur METER e voltage ut current us single half sine	nless otherwise	SYMBOL V <sub>RRM</sub> V <sub>DC</sub>		150 150 15 15		V V
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpr Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge 0	D ELECTRICA emperature ur METER e voltage ut current is single half sine Current	nless otherwise @T <sub>c</sub> =125°C -wave @tp=2us	SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub> I <sub>RRM</sub>		150 150 15 150 3		V V A A A
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpi Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge 0 Operating junction and Storage 7	D ELECTRICA emperature ur METER e voltage ut current is single half sine Current Femperature rang	nless otherwise @T <sub>c</sub> =125°C -wave @tp=2us	SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub>		150 150 15 15		V V A A
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outp Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge ( Operating junction and Storage T STATIC ELECTRICAL CH	D ELECTRICA emperature ur METER e voltage ut current is single half sine Current Femperature rang HARACTERIS	nless otherwise @Tc=125°C -wave @tp=2us Je STICS	SYMBOL VRRM VDC I(AV) IFSM IRRM TJ, TSTG		150 150 15 150 3 -55 ~ +150		V V A A A A C
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpi Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge 0 Operating junction and Storage 1	D ELECTRICA emperature ur METER e voltage ut current is single half sine Current Femperature rang HARACTERIS	aless otherwise	SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub> I <sub>RRM</sub>	MIN	150 150 15 150 3 -55 ~ +150 <b>TYP</b>	MAX	V V A A A
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpr Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge C Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER	D ELECTRICA emperature ur METER e voltage ut current is single half sine Current Femperature rang HARACTERIS	@T <sub>c</sub> =125°C -wave @tp=2us ge STICS CONDITIONS T_J=25°C	SYMBOL VRRM VDC I(AV) IFSM IRRM TJ, TSTG	MIN	150 150 15 150 3 -55 ~ +150 <b>TYP</b> 0.84	0.86	V V A A A A C
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpi Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge C Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4)	D ELECTRICA emperature ur METER e voltage ut current is single half sine Current Femperature rang HARACTERIS IF=15A	@T <sub>c</sub> =125°C -wave @tp=2us je STICS CONDITIONS T_J=25°C T_J=125°C	e specified.          SYMBOL         V <sub>RRM</sub> V <sub>DC</sub> I(AV)         I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub>		150 150 15 150 3 -55 ~ +150 <b>TYP</b> 0.84 0.68	0.86 0.75	V           V           A           A           °C           UNIT           V
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpi Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge C Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4)	D ELECTRICA emperature ur METER e voltage ut current is single half sine Current Femperature rang HARACTERIS	@T <sub>c</sub> =125°C -wave @tp=2us ge STICS CONDITIONS T_J=25°C	e specified.          SYMBOL         V <sub>RRM</sub> V <sub>DC</sub> I(AV)         I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub>		150 150 15 150 3 -55 ~ +150 <b>TYP</b> 0.84	0.86	V V A A A C UNIT
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpr Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge C Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER	D ELECTRICA emperature ur METER e voltage ut current is single half sine Current Femperature rang HARACTERIS IF=15A	@T <sub>c</sub> =125°C -wave @tp=2us ge STICS CONDITIONS T_J=25°C T_J=125°C T_J=25°C	e specified.          SYMBOL         V <sub>RRM</sub> V <sub>DC</sub> I(AV)         I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL         V <sub>F</sub>		150 150 15 150 3 -55 ~ +150 <b>TYP</b> 0.84 0.68	0.86 0.75 20	V V A A A O C UNIT V UNIT
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outp Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge C Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4) Reverse Current Breakdown voltage	DELECTRICA emperature un METER e voltage ut current is single half sine Current Temperature rang HARACTERIS IF=15A $V_R=150V$ $I_R=100uA$	hless otherwise $@T_c=125^{\circ}C$ -wave @tp=2us ge <b>STICS</b> <b>SONDITIONS</b> $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$	e specified. V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL V <sub>F</sub> I <sub>R</sub>		150 150 15 150 3 -55 ~ +150 <b>TYP</b> 0.84 0.68  0.71	0.86 0.75 20 10	V V A A A O C UNIT V UNIT V uA mA
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outp Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge 0 Operating junction and Storage 1 STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4) Reverse Current Breakdown voltage DYNAMIC ELECTRICAL C	DELECTRICA emperature un METER e voltage ut current is single half sine Current Femperature rang HARACTERIS IF=15A $V_R=150V$ $I_R=100uA$ CHARACTER	hless otherwise $@T_c=125^{\circ}C$ -wave @tp=2us ge <b>STICS</b> <b>SONDITIONS</b> $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$	e specified. SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL V <sub>F</sub> I <sub>R</sub> V <sub>B</sub>		150 150 15 150 3 -55 ~ +150 <b>TYP</b> 0.84 0.68  0.71 	0.86 0.75 20 10	V V A A A C C UNIT V UNIT V UNIT V V
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpu Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge ( Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4) Reverse Current Breakdown voltage DYNAMIC ELECTRICAL ( PARA	D ELECTRICA emperature un METER e voltage ut current is single half sine Current Temperature rang IARACTERIS IF=15A $V_R=150V$ $I_R=100uA$ CHARACTER	hless otherwise $@T_c=125^{\circ}C$ -wave @tp=2us ge <b>STICS</b> <b>SONDITIONS</b> $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$	e specified. SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL V <sub>F</sub> I <sub>R</sub> V <sub>B</sub>		150 150 15 150 3 -55~+150 <b>TYP</b> 0.84 0.68  0.71 	0.86 0.75 20 10	V           V           A           A           O°C           UNIT           V           uA           MA           V           UNIT           UNIT
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpu Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge ( Operating junction and Storage 1 STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4) Reverse Current Breakdown voltage DYNAMIC ELECTRICAL ( PARA Typical junction capacitance (Note 1)	DELECTRICA emperature un METER e voltage ut current is single half sine Current Temperature rang HARACTERIS Ir=15A $V_R=150V$ $I_R=100uA$ CHARACTER AMETER ote 5)	hless otherwise $@T_c=125^{\circ}C$ -wave @tp=2us ge <b>STICS</b> <b>SONDITIONS</b> $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$	e specified. SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL V <sub>F</sub> I <sub>R</sub> V <sub>B</sub>		150 150 15 150 3 -55 ~ +150 <b>TYP</b> 0.84 0.68  0.71 	0.86 0.75 20 10	V V A A A C C UNIT V UNIT V UNIT V V
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpi Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge C Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4) Reverse Current Breakdown voltage DYNAMIC ELECTRICAL CH PARA Typical junction capacitance (Note THERMAL CHARACTER	D ELECTRICA emperature un METER e voltage ut current is single half sine Current Femperature rang HARACTERIS IF=15A $V_R=150V$ $I_R=100uA$ CHARACTER METER ote 5) ISTICS	hless otherwise $@T_c=125^{\circ}C$ -wave @tp=2us ge <b>STICS</b> <b>SONDITIONS</b> $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$	e specified. SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL V <sub>F</sub> I <sub>R</sub> V <sub>B</sub> SYMBOL C <sub>J</sub>		150 150 15 150 3 -55 ~ +150 <b>TYP</b> 0.84 0.68  0.71  <b>TYP</b> 905	0.86 0.75 20 10	V V A A A C C UNIT V UNIT pF
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpi Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge C Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4) Reverse Current Breakdown voltage DYNAMIC ELECTRICAL CH PARA Typical junction capacitance (Note THERMAL CHARACTER	DELECTRICA emperature un METER e voltage ut current is single half sine Current Temperature rang HARACTERIS Ir=15A $V_R=150V$ $I_R=100uA$ CHARACTER AMETER ote 5)	hless otherwise $@T_c=125^{\circ}C$ -wave @tp=2us ge <b>STICS</b> <b>SONDITIONS</b> $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$	e specified. SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I(AV) I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL V <sub>F</sub> I <sub>R</sub> V <sub>B</sub> SYMBOL C <sub>J</sub>		150 150 15 150 3 -55 ~ +150  0.71  TYP 905 TYP	0.86 0.75 20 10	V V A A A C C V UNIT V UNIT pF
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpi Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge C Operating junction and Storage T STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4) Reverse Current Breakdown voltage DYNAMIC ELECTRICAL CH PARA Typical junction capacitance (Note THERMAL CHARACTER	DELECTRICA emperature un METER e voltage ut current is single half sine Current Temperature rang HARACTERIS IF=15A $V_R=150V$ $I_F=150V$ $I_R=100uA$ CHARACTER AMETER ote 5) ISTICS METER	hless otherwise $@T_c=125^{\circ}C$ -wave @tp=2us ge <b>STICS</b> <b>SONDITIONS</b> $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$	e specified. SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I <sub>(AV)</sub> I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL V <sub>F</sub> I <sub>R</sub> V <sub>B</sub> SYMBOL C <sub>J</sub> SYMBOL RthJ <sub>c</sub>		150 150 15 150 3 -55~+150  0.71   TYP 905  905 2	0.86 0.75 20 10	V           V           A           A           O°C           UNIT           V           uA           MA           V           UNIT           UNIT
MAXIMUM RATINGS ANI Ratings at 25°C ambient to ABSOLUTE RATINGS Maximum repetitive peak reverse Maximum DC blocking voltage Maximum Average rectified outpu Peak forward surge current 8.3m superimposed on rated load. Peak Repetitive Reverse Surge ( Operating junction and Storage 1 STATIC ELECTRICAL CH PARAMETER Forward voltage (Note 4) Reverse Current Breakdown voltage DYNAMIC ELECTRICAL ( PARA Typical junction capacitance (Note THERMAL CHARACTER PARA	DELECTRICA emperature un METER e voltage ut current is single half sine Current Temperature rang HARACTERIS IF=15A $V_R=150V$ $I_F=150V$ $I_R=100uA$ CHARACTER AMETER ote 5) ISTICS METER	hless otherwise $@T_c=125^{\circ}C$ -wave @tp=2us ge <b>STICS</b> <b>SONDITIONS</b> $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$ $T_J=25^{\circ}C$	e specified. SYMBOL V <sub>RRM</sub> V <sub>DC</sub> I(AV) I <sub>FSM</sub> I <sub>RRM</sub> T <sub>J</sub> , T <sub>STG</sub> SYMBOL V <sub>F</sub> I <sub>R</sub> V <sub>B</sub> SYMBOL C <sub>J</sub>		150 150 15 150 3 -55 ~ +150  0.71  TYP 905 TYP	0.86 0.75 20 10	V V A A A C C UNIT V UNIT pF UNIT

See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</li>
 300us pulse width, 2% duty cycle.
 Measured at 1.0MHz and applied voltage of 4.0V DC.
 Thermal resistance test performed in accordance with JESD-51.
 The unit mounted on Copper heatsink 60mm x 60mm x 1.7mm.

**RATING AND CHARACTERISTIC CURVES** G15H150D5

#### LITE-ON SEMICONDUCTOR

100

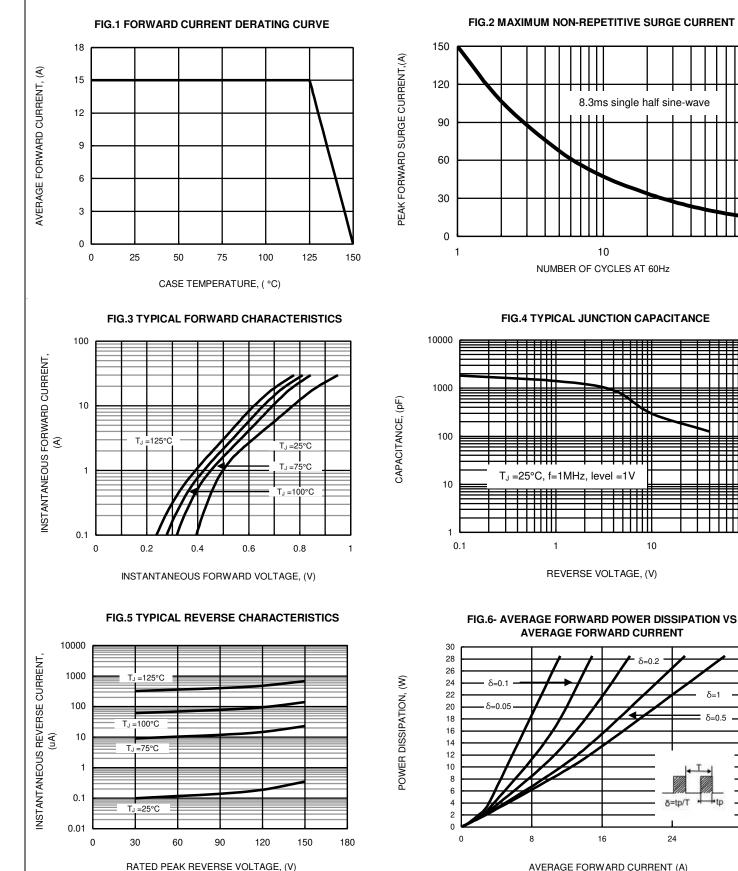
100

δ=1

δ=0.5

to

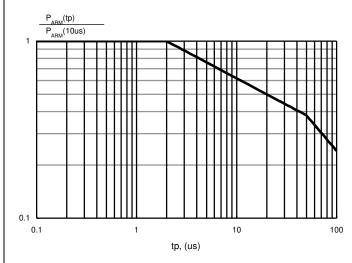
32



AVERAGE FORWARD CURRENT (A)



#### FIG.7- NORMALIZED AVALANCHE POWER DERATING VERSUS PULSE DURATION



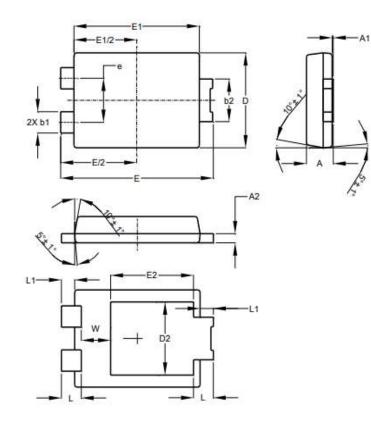


# Ordering Information :

	Part Number	Deekere	Pa	acking
	Part Number	Package	Qty.	Carrier
	G15H150D5	PowerDI5	5000	Tape & Reel
arking inforn	Logo Product Type Marking Code	LT YXWW G15H150	X: Ma	ode ear code anufacturer's Internal o Week code

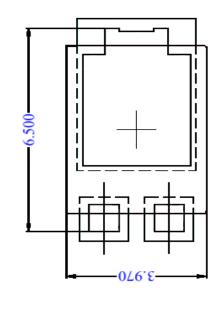


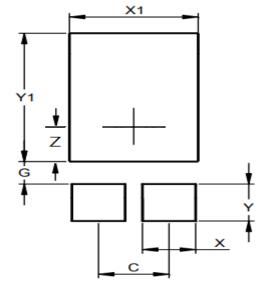
## Suggested Package:



PowerDI5							
DIM.	MIN.	MAX	TYP				
Α	1.05	1.15	1.10				
A1	0	0.05					
A2	0.33	0.43	0.381				
b1	0.80	0.99	0.89				
b2	1.70	1.88	1.78				
D	3.90	4.05	3.966				
D2			3.05				
Е	6.40	6.60	6.51				
е	1	1.84 NOI	M				
E1	5.30	5.45	5.37				
E2			3.549				
L	0.75	0.95	0.85				
L1	0.50	0.65	0.57				
W	1.10	1.41	1.255				
All d	limensio	n in millii	meter				

## Soldering Pad Layout :

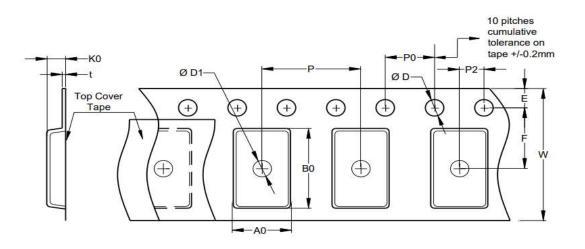




Dimensions	Value (mm)
С	1.840
G	0.852
Х	1.390
X1	3.360
Y	1.400
Z	1.310
Y1	4.860



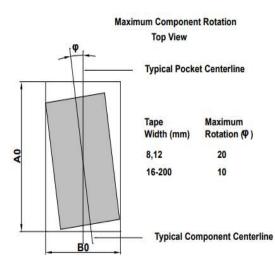
#### **Embossed Carrier Dimensions**

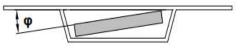


#### **EMBOSSED TYPE**

Unit:mm

TYPE SIZE	A0	B0	D	D1	E	F
	4.225±0.106	6.845±0.115	1.55±0.05	1.50±0.25	1.75±0.10	7.50±0.10
16mm	K0	Р	P0	P2	t	
	1.290±0.120	8.00±0.10	4.00±0.10	2.00±0.05	0.290±0.060	

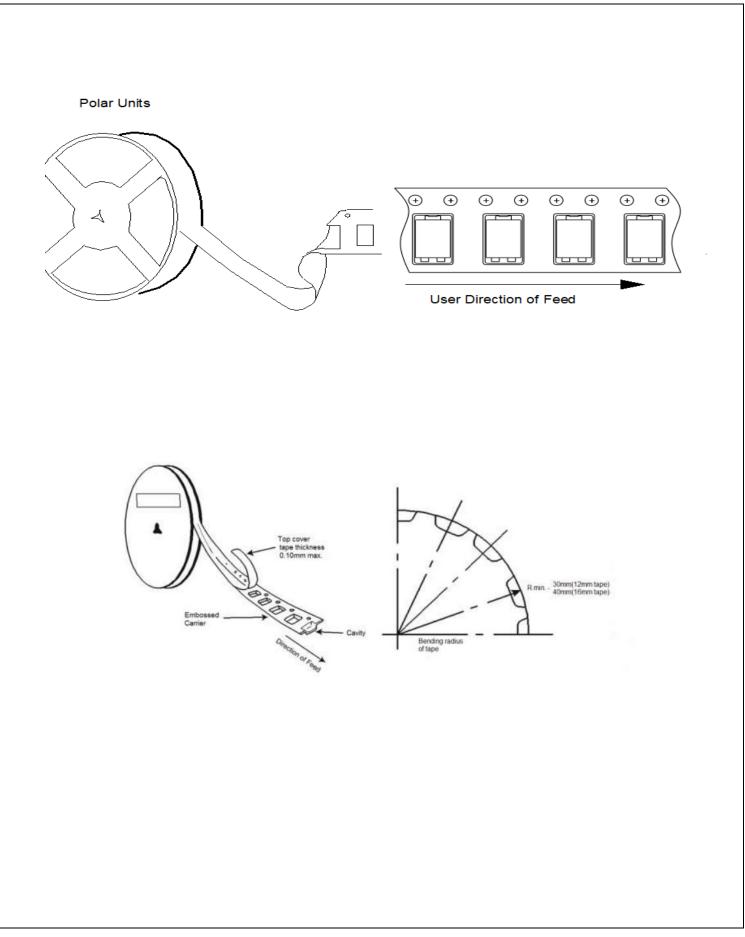




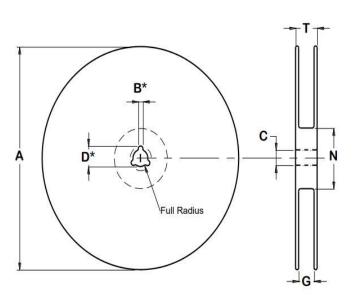
Tape Width (mm)	Maximum Rotation (Φ)
8,12	20
16-56	10
72-200	5

PACKAGE AND PACKING INFORMATION G15H150D5

### LITE-ON SEMICONDUCTOR







#### **REEL DIMENSIONS**

#### Unit:mm

TAPE SIZE	Reel Size	А	B MAX	С	D MAX	N MIN	G	T MAX
16mm	13"	330±2	2.0+0.5/-0	13+0.5/-0.2	20.5±0.2	100±2	16.4+2.0/-0	22.4

#### PACKING

Reel SIZE	Q'TY/REEL	BOX SIZE	Q'TY/BOX	CARTON SIZE	Q'TY/CARTON
	( PCS )	(mm)	(PCS)	(mm)	( PCS )
13"	5K			335X335X310	60K



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